

IN THE DRAWINGS:

The attached sheets of drawings include changes to Figs. 2, 3, 6, 9D, 12, 13A and 13B to correct minor errors in these figures.

Attachment: Replacement Sheets (being submitted with corrected formal drawings)

Annotated Sheets Showing Changes

REMARKS

Applicant is merely amending the figures herein to correct minor errors in the figures, as follows:

In Fig. 2, line S4 has been amended to show "(4,4)" and not "(4,3)" (see e.g. page 5, lns. 23-24 of the specification).

In Fig. 3, nodes are being added for (2,640) and (480,640).

In Fig. 6, nodes are being added for (2, n) and (m,n).

In Fig. 9D, "1028a" has been amended to "6028a" (see page 22, ln. 6).

In Fig. 12, "218" has been amended to "818" (see page 27, ln. 22).

In Fig. 13A, the spelling of "impurity" has been corrected.

In Fig. 13B, 4104 has been amended to recite "benzocyclobutene(BCB)" (see page 29, ln. 17).

Hence, no new matter is being added. Therefore, it is respectfully requested that this amendment be entered.

If any fee is due for this amendment, please charge our deposit account 50/1039.

Favorable consideration is earnestly solicited.

Respectfully submitted,



Mark J. Murphy
Registration No. 34,225

COOK, ALEX, McFARRON, MANZO,
CUMMINGS & MEHLER, Ltd.
200 West Adams Street, Suite 2850
Chicago, Illinois 60606
(312) 236-8500

Customer no. 000026568

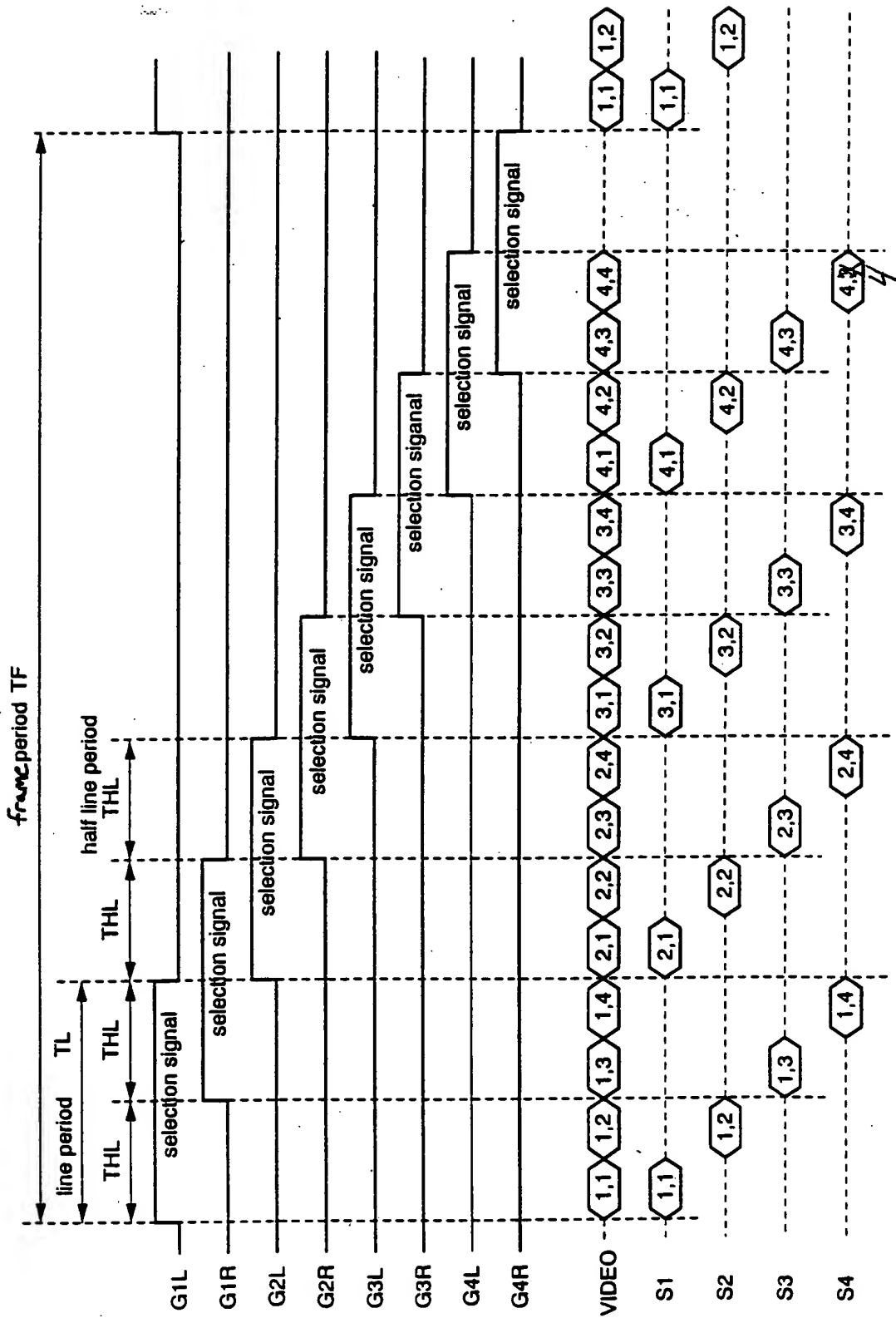


Fig.2

Marked-up
copy



2000

liquid crystal display device

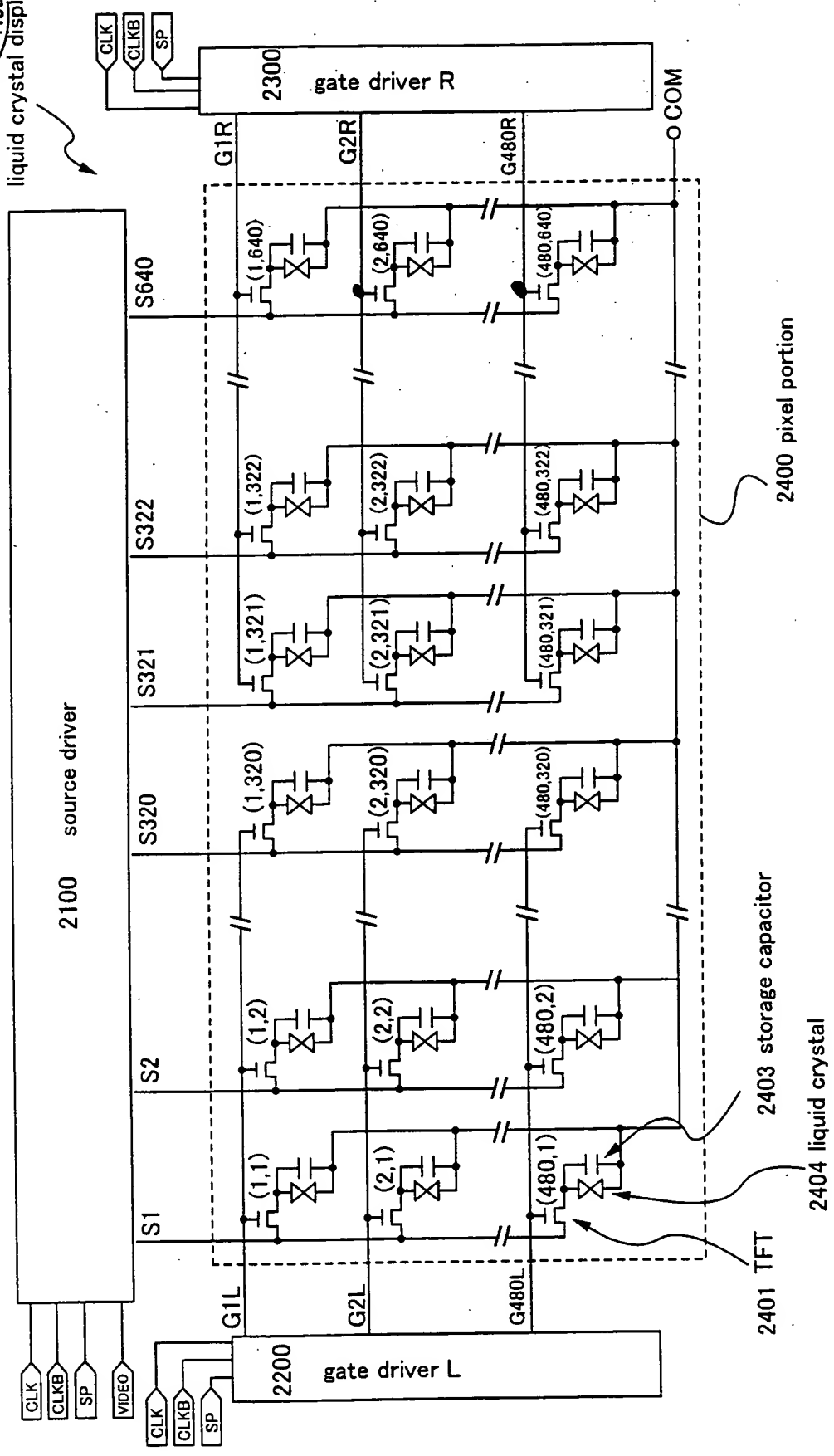


Fig.3

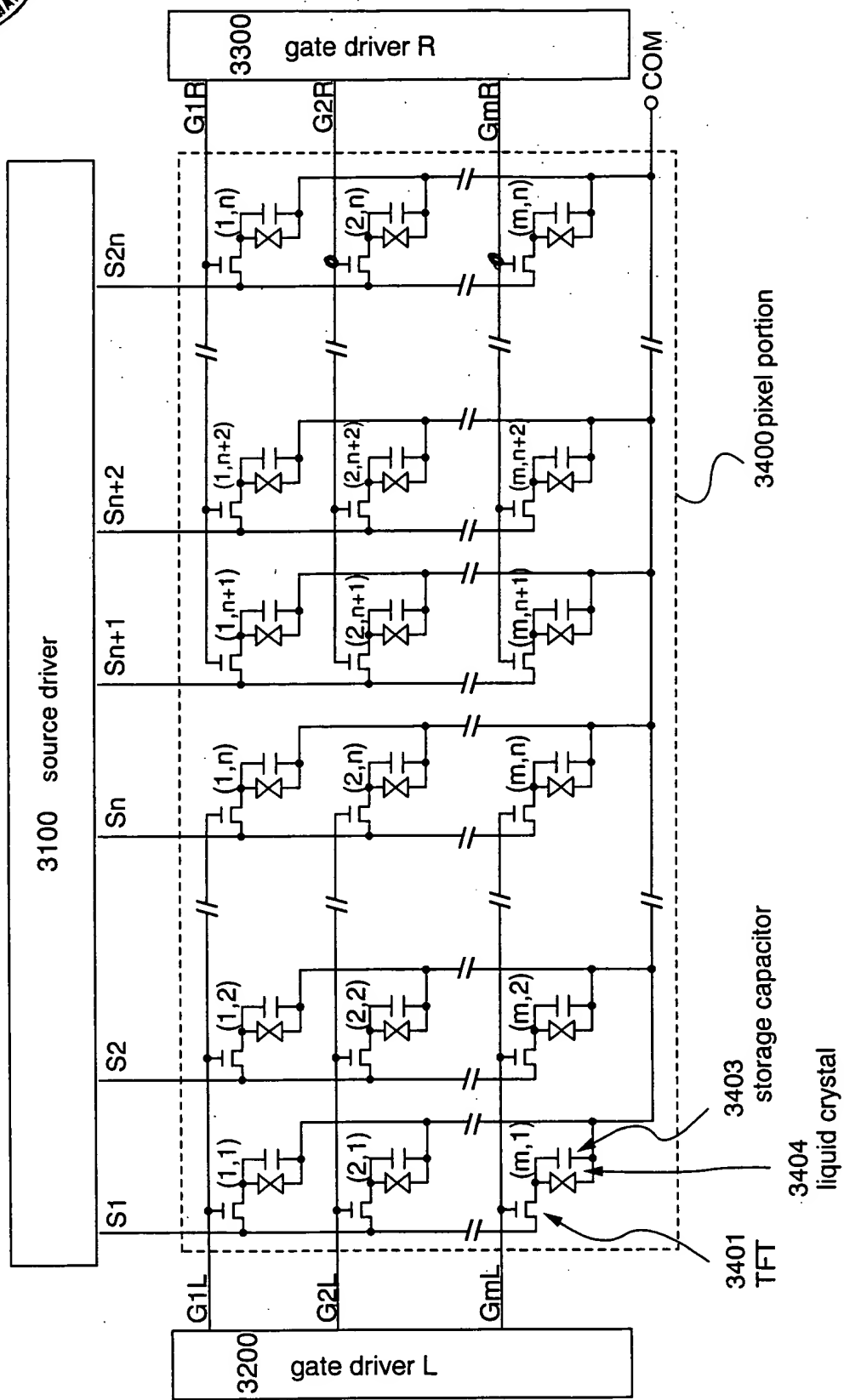


Fig.6

Marked copy

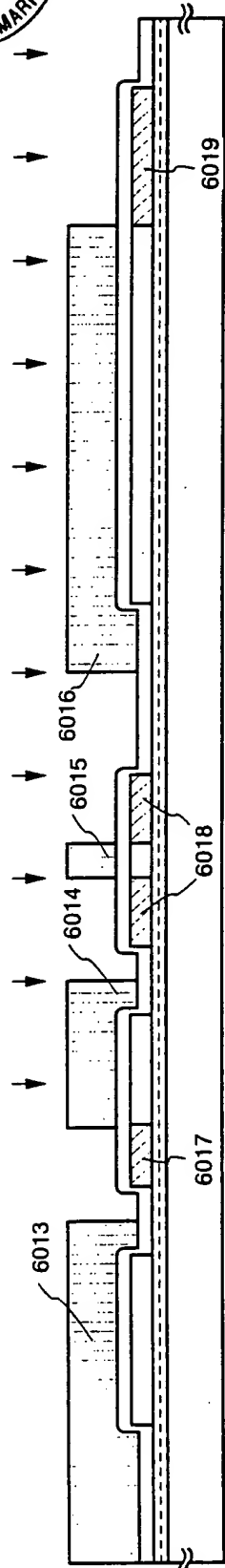


Fig. 9A

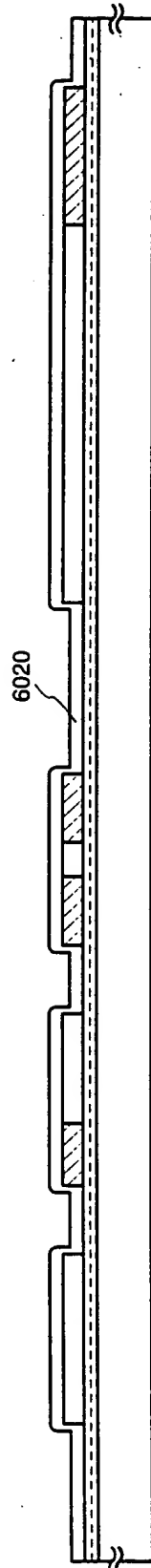


Fig. 9B

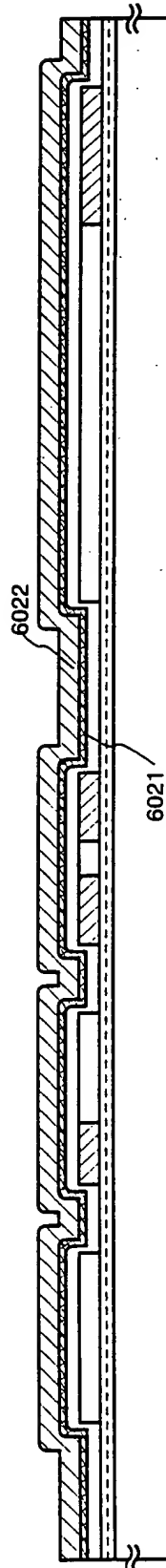


Fig. 9C

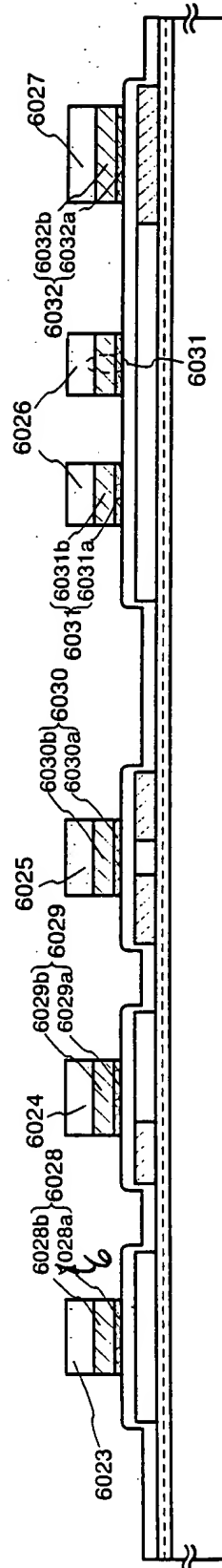


Fig. 9D

Marked-up
copy

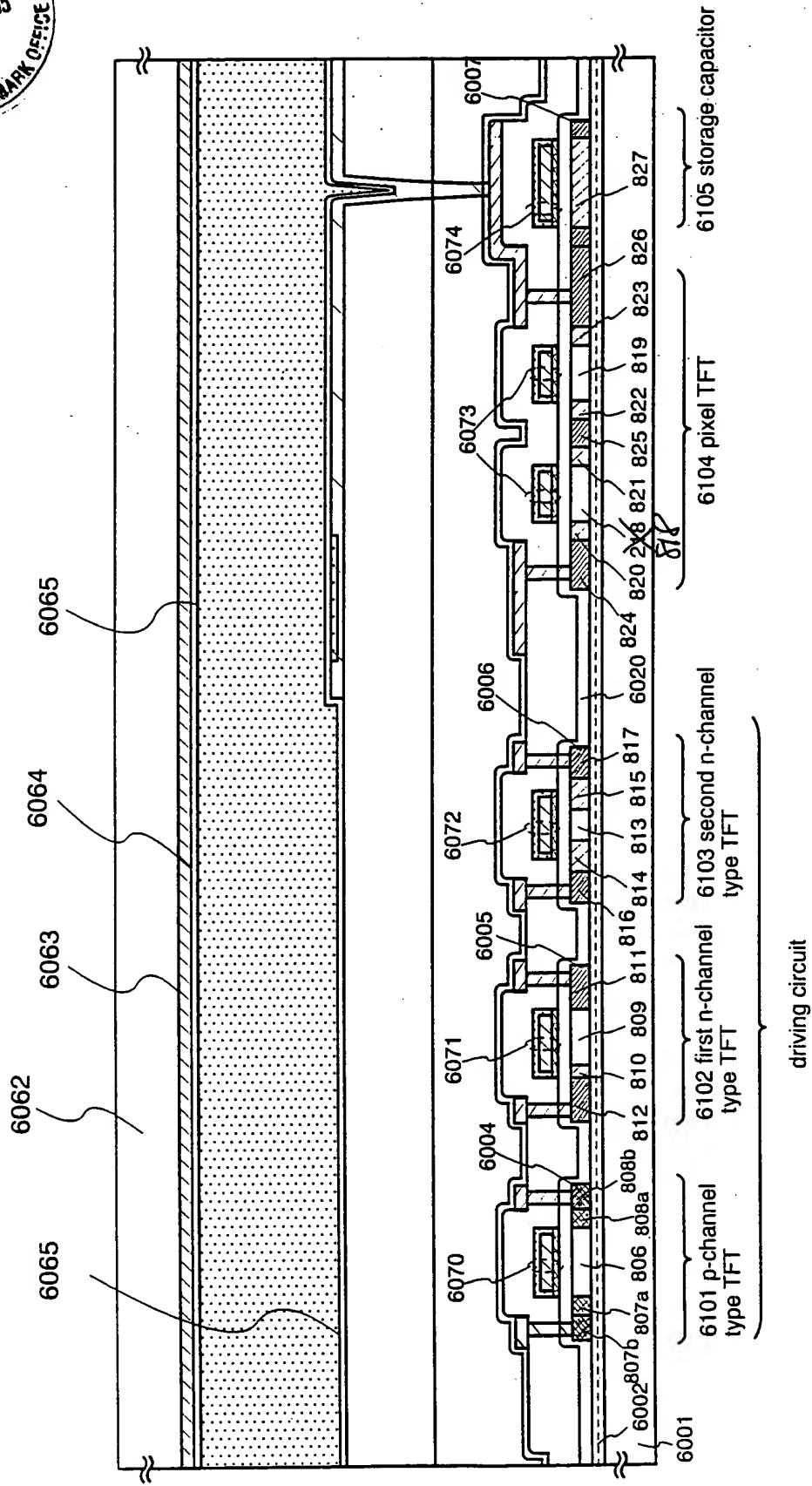
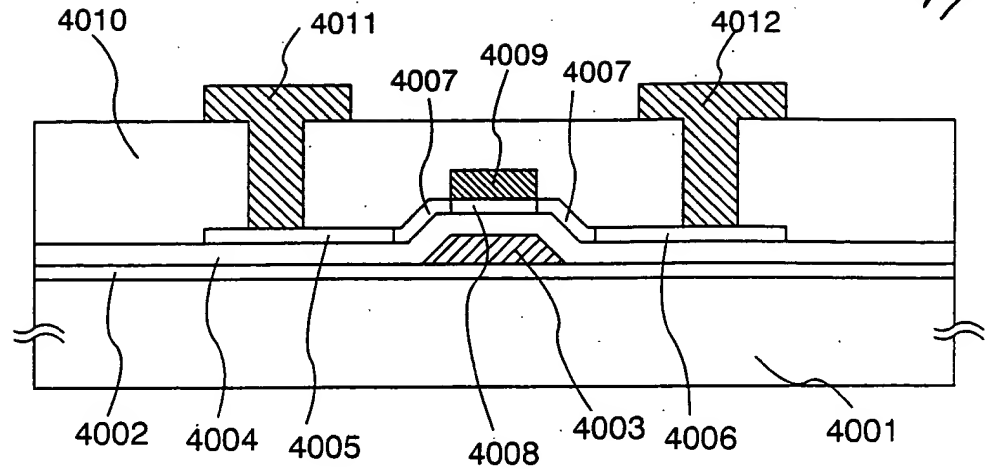


Fig.12



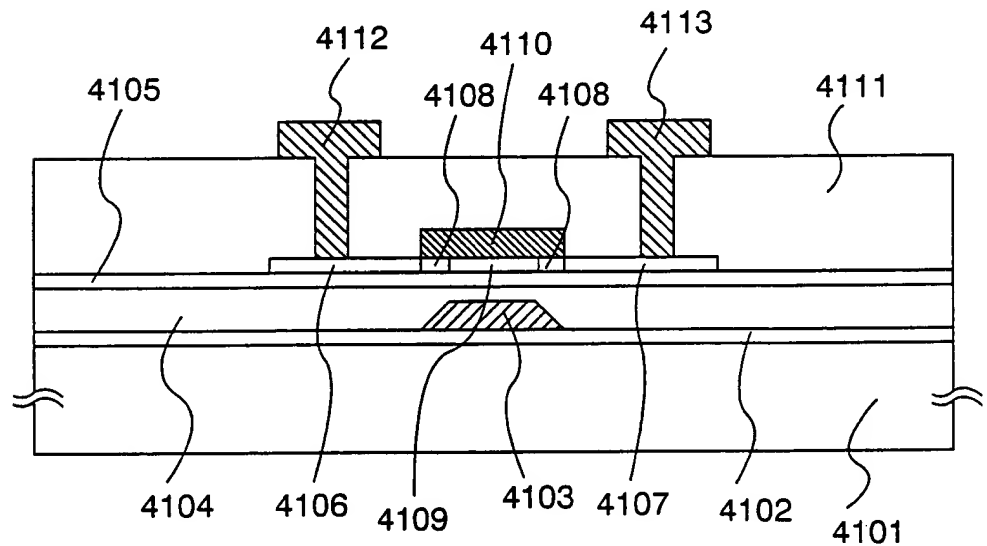
Marked-up
copy

Fig.13A



- | | |
|---------------------------|--|
| 4001 substrate | 4007 low concentration impurity region(LDD region) |
| 4002 silicon oxide film | 4008 channel forming region |
| 4003 gate electrode | 4009 channel protective film |
| 4004 gate insulating film | 4010 interlayer insulating film |
| 4005 source region | 4011 source electrode |
| 4006 drain region | 4012 drain electrode |

Fig.13B



- | | |
|---------------------------|--|
| 4101 substrate | 4108 low concentration impurity region(LDD region) |
| 4102 silicon oxide film | 4109 channel forming region |
| 4103 gate electrode | 4110 channel protecting film |
| 4104 bezocyclobutene(BCB) | 4111 interlayer insulating film |
| 4105 silicon nitride film | 4112 source electrode |
| 4106 source region | 4113 drain electrode |
| 4107 drain region | |